

# Geoffrey Avit

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Record Pure Zincblende Phase in GaAs Nanowires down to 5 nm in Radius. Nano Letters, 2014, 14, 3938-3944.	4.5	82
2	Ultralong and Defect-Free GaN Nanowires Grown by the HVPE Process. Nano Letters, 2014, 14, 559-562.	4.5	58
3	Circumventing the miscibility gap in InGaN nanowires emitting from blue to red. Nanotechnology, 2018, 29, 465602.	1.3	22
4	Influence of Silicon on the Nucleation Rate of GaAs Nanowires on Silicon Substrates. Journal of Physical Chemistry C, 2018, 122, 19230-19235.	1.5	15
5	Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708.	1.3	13
6	Compositional control of homogeneous InGaN nanowires with the In content up to 90%. Nanotechnology, 2019, 30, 044001.	1.3	12
7	Vapor liquid solid-hydride vapor phase epitaxy (VLS-HVPE) growth of ultra-long defect-free GaAs nanowires: Ab initio simulations supporting center nucleation. Journal of Chemical Physics, 2014, 140, 194706.	1.2	11
8	GaN Rods Grown on Si by SAG-HVPE toward GaN HVPE/InGaN MOVPE Core/Shell Structures. Crystal Growth and Design, 2016, 16, 2509-2513.	1.4	8
9	Crystal engineering by tuning the growth kinetics of GaN 3-D microstructures in SAG-HVPE. CrystEngComm, 2018, 20, 6207-6213.	1.3	6
10	Formation of voids in selective area growth of InN nanorods in SiN <sub>x</sub> on GaN templates. Nano Futures, 2020, 4, 025002.	1.0	5
11	Morphological Control of InN Nanorods by Selective Area Growth—Hydride Vapor-Phase Epitaxy. Crystal Growth and Design, 2020, 20, 2232-2239.	1.4	5